

CLAIMS:

1-15. (Canceled)

16. (Currently amended) A method for chemical vapor deposition comprising supplying a plurality of chambers with reactant gases from a common gas supply, individually controlling amounts of components of the reactant gases directly provided to each of the chambers with gas flow controllers independently from each other, and removing gas from the chambers via a common gas exhaust system,

~~wherein a wafer carrier is disposed within each one of the plurality of chambers, wherein the wafer carrier and a top portion of each chamber cooperate to define a generally flat, continuous and unobstructed flow channel such that rotating the wafer carrier effects generally laminar flow of gas through the flow channel intermediate the top portion of each chamber and the wafer carrier.~~

wherein the chambers are supplied with reactant gas via gas inlets that are substantially flush with tops of the chambers and the reactant gas flows through narrow gas channels of the chambers such that laminar flow of the reactant gas is substantially maintained within the chambers.

17-130. (Cancelled)

131. (Currently amended) A method for chemical vapor deposition, the method comprising:

providing a plurality of reactor chambers;

providing reaction gases to the chambers via a common gas supply;

individually controlling amounts of components of the reaction gases directly provided to each of the chambers with gas controllers independently from each other; and

removing gases from the chambers via a common gas exhaust system,
~~wherein a wafer carrier is disposed within each one of the plurality of reactor chambers, wherein the wafer carrier and a top portion of each reactor chamber cooperate to define a generally flat, continuous and unobstructed flow channel such that rotating the wafer carrier effects generally laminar flow of gas through the flow channel intermediate the top portion of each chamber and the wafer carrier.~~

wherein the chambers are supplied with reactant gas via gas inlets that are substantially flush with tops of the chambers and the reactant gas flows through narrow gas channels of the chambers such that laminar flow of the reactant gas is substantially maintained within the chambers.

132. (Previously presented) The method as recited in claim 131, further comprising supporting less than twelve wafers upon the wafer carrier disposed within each chamber.

133-160. (Canceled)